TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX162374FT

Low-Voltage 16-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

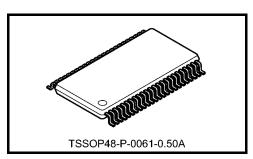
The TC74VCX162374FT is a high-performance CMOS 16-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V$.

This 16-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. When the \overline{OE} input is high, the outputs are in a high-impedance state.

The $26 \cdot \Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

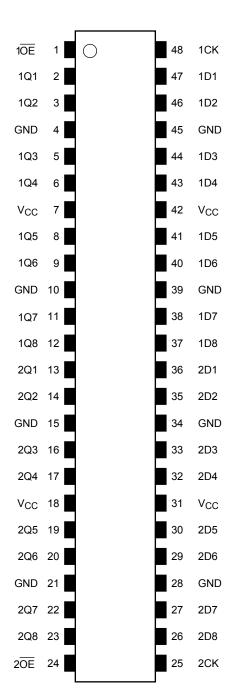


Weight: 0.25 g (typ.)

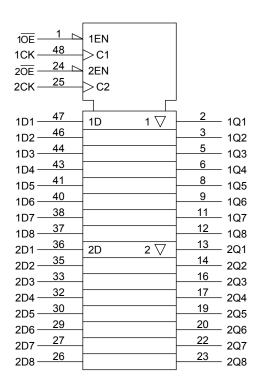
Features

- 26-Ω series resistors on outputs
- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 3.4 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V})$
 - : $t_{pd} = 4.8 \text{ ns (max)} (V_{CC} = 2.3 \text{ to } 2.7 \text{ V})$
 - : $t_{pd} = 6.0 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$
 - : $I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$
 - : $I_{OH}/I_{OL} = \pm 4$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$
 - Human body model $\geq \pm 2000 \text{ V}$
- Package: TSSOP
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

	Outputs		
1OE	1CK	1D1-1D8	1Q1-1Q8
Н	Х	Х	Z
L	\rightarrow	Х	Qn
L		L	L
L,		Н	Н

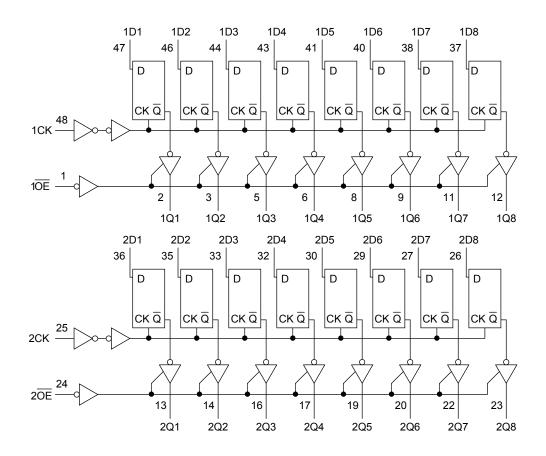
	Outputs		
2 OE	2CK	2D1-2D8	2Q1-2Q8
Н	Х	Х	Z
L	$\overline{}$	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Qn: No change

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC output voltage	V_{OUT}	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I_{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol Rating		Unit
Power supply voltage	Voc	1.8 to 3.6	V
rower supply voltage	V _{CC}	1.2 to 3.6 (Note 2)	V
Input voltage	V _{IN}	-0.3 to 3.6	V
Output voltage	V _{OUT}	0 to 3.6 (Note 3)	V
Output voltage	VOU1	0 to V _{CC} (Note 4)	V
		±12 (Note 5)	
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{CC} \le 3.6$ V)

Character	istics	Symbol	Test C	Test Condition		Min	Max	Unit	
					V _{CC} (V)				
Input voltage	H-level	V_{IH}	-	_	2.7 to 3.6	2.0		V	
input voltage	L-level	V _{IL}		_	2.7 to 3.6		0.8	٧	
				$I_{OH} = -100 \mu A$	2.7 to 3.6	V _{CC} - 0.2	_		
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_		
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_		
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2	_	V	
			V _{OL} V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 100 \mu A$	2.7 to 3.6		0.2		
	L-level	Vai		$I_{OL} = 6 \text{ mA}$	2.7	_	0.4		
	L-level	VOL		AIN - AIH OL AIT	$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8		
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μА	
2 state output OFF	atata aurrant	1	V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH}$ or V_{IL}			±10.0		
3-state output OFF state current		loz	$V_{OUT} = 0$ to 3.6 V		2.7 to 3.6		±10.0	μΑ	
Power-off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА	
Ouise sent supply supply		Icc	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0		
Quiescent supply o	Quiescent supply current		$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7 to 3.6	_	±20.0	μΑ	
Increase in I _{CC} per	input	Δlcc	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	_	750		

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteris	stics	Symbol	Test Co	Test Condition Vcc (V)		Min	Max	Unit
land to the ma	H-level	V _{IH}	_	_	2.3 to 2.7	1.6	_	
Input voltage	L-level	V _{IL}	_	_	2.3 to 2.7	_	0.7	V
				$I_{OH} = -100 \mu A$	2.3 to 2.7	V _{CC} - 0.2	_	
	H-level	VoH	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -4 mA	2.3	2.0	_	
				I _{OH} = -6 mA	2.3	1.8	_	
Output voltage				I _{OH} = -8 mA	2.3	1.7	_	V
				I _{OL} = 100 μA	2.3 to 2.7	_	0.2	
	L-level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6	
Input leakage currer	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μΑ
3-state output OFF state current		loz	$V_{IN} = V_{IH}$ or V_{IL}		2.3 to 2.7	_	±10.0	μА
			V _{OUT} = 0 to 3.6 V					
Power-off leakage c	urrent	loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Quiescent supply cu	ırrent	Icc	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	μΑ
Quiococin ouppiy oc		.00	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3 to 2.7	_	±20.0	μ/ (



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	etice	Symbol	Test Condition			Min	Max	Unit
Ondracteris	51103	Cymbol	1031 00	onation	V _{CC} (V)	IVIIII	IVICX	Offic
Input voltage	H-level	V _{IH}	_	_	1.8 to 2.3	0.7 × V _{CC}	_	V
input voltage	L-level	V _{IL}	_	_	1.8 to 2.3	_	0.2 × V _{CC}	V
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				I _{OH} = -4 mA	1.8	1.4	_	V
	L-level	Vol	V _{IN} = V _{IH} or V _{II}	I _{OL} = 100 μA	1.8		0.2	
	L-IEVEI	VOL	VIN — VIH OI VIL	I _{OL} = 4 mA	1.8		0.3	
Input leakage currer	nt	I _{IN}	$V_{IN} = 0 \text{ to } 3.6 \text{ V}$		1.8		±5.0	μΑ
3-state output OFF	state current	l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$				±10.0	μА
Power-off leakage c	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Ouissant summit summer		laa	$V_{IN} = V_{CC}$ or GND		1.8		20.0	μА
Quiescent supply cu	iii c iii	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6$	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$			±20.0	μΑ



AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
Citalacteristics	Symbol	rest Condition	V _{CC} (V)	IVIIII	IVIAX	Offic
			1.8	125	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
Drang ration delay time			1.8	1.5	6.0	
Propagation delay time (CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	4.8	ns
(CK-Q)	t _{pHL}		3.3 ± 0.3	0.8	3.4	
			1.8	1.5	7.6	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	1.0	5.4	ns
	^t pZH		3.3 ± 0.3	0.8	3.9	
		Figure 1, Figure 3	1.8	1.5	5.3	
3-state output disable time	t _{pLZ}		2.5 ± 0.2	1.0	4.4	ns
	t _{pHZ}		3.3 ± 0.3	0.8	4.0	
NATIONAL CONTRACTOR OF THE PROPERTY OF THE PRO			1.8	3.0	_	
Minimum pulse width		t _{w (L)} Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
(CK)	^t w (L)		3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum setup time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	tosLH	(Note 2)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

Note 1: For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	Ī	V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	0.15	
Quiet output maximum dynamic V _{OI}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	0.25	V
, 01		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	-0.15	
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	-0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	1.55	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	3.3	2.65	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

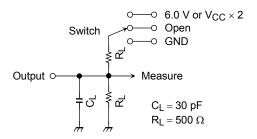
Characteristics	Cymbol	Test Condition			Tun	Unit
Characteristics	Symbol			V _{CC} (V)	Тур.	Offic
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$	Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

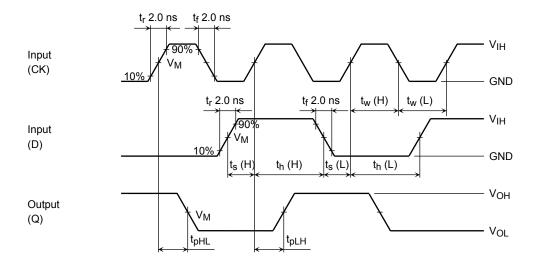


Figure 2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

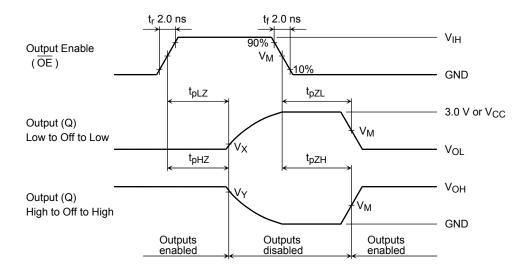
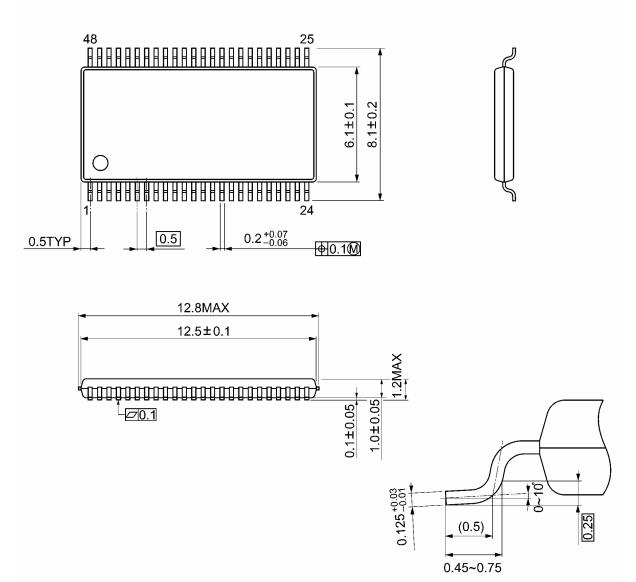


Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol		V _{CC}	
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V_{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
V_{Y}	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions

TSSOP48-P-0061-0.50A Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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